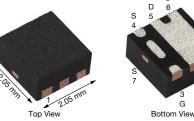
SiA483DJ

www.vishay.com

P-Channel 30 V (D-S) MOSFET

PowerPAK[®] SC-70-6L Single





Marking code: BY

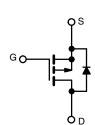
| PRODUCT SUMMARY | | | | | |
|---|--------|--|--|--|--|
| V _{DS} (V) | -30 | | | | |
| $R_{DS(on)}$ max. (Ω) at V_{GS} = -10 V | 0.021 | | | | |
| $R_{DS(on)}$ max. (Ω) at V_{GS} = -4.5 V | 0.030 | | | | |
| Q _g typ. (nC) | 21 | | | | |
| I _D (A) ^a | -12 | | | | |
| Configuration | Single | | | | |

FEATURES

- TrenchFET[®] power MOSFET
- Thermally enhanced PowerPAK[®] SC-70 package
 - Small footprint area
- Low on-resistance
- 100 % R_q tested
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- Smart phones, tablet PCs, mobile computing:
 - Battery switches
 - Load switches
 - Power management
 - DC/DC converters



RoHS

COMPLIANT

HALOGEN FREE



| | ORDERING INFORMATION |
|---|----------------------|
| 1 | |

| Package | PowerPAK SC-70 |
|---------------------------------|-----------------|
| Lead (Pb)-free and halogen-free | SiA483DJ-T1-GE3 |
| | |

| ABSOLUTE MAXIMUM RATINGS | (T _A = 25 °C, unless | s otherwise note | d) | | |
|--|---------------------------------|-----------------------------------|----------------------|------|--|
| PARAMETER | | SYMBOL | LIMIT | UNIT | |
| Drain-source voltage | | V _{DS} | -30 | V | |
| Gate-source voltage | | V _{GS} | ± 20 | | |
| Continuous drain current (T _J = 150 °C) | T _C = 25 °C | | -12 ^a | | |
| | T _C = 70 °C | | -12 ^a | | |
| | T _A = 25 °C | I _D | -10 ^{b, c} | | |
| | T _A = 70 °C | | -8 ^{b, c} | A | |
| Pulsed drain current (t = 300 µs) | | I _{DM} | -40 | | |
| Continuous source-drain diode current | T _C = 25 °C | | -12 ^a | | |
| Continuous source-drain diode current | T _A = 25 °C | I _S | -2.9 ^{b, c} | | |
| | T _C = 25 °C | | 19 | | |
| Maximum power dissipation | T _C = 70 °C | | 12 | w | |
| | T _A = 25 °C | P _D | 3.5 ^{b, c} | vv | |
| | T _A = 70 °C | | 2.2 ^{b, c} | | |
| Operating junction and storage temperature range | | T _J , T _{stg} | -55 to +150 | °C | |
| Soldering recommendations (peak temperature |) d, e | | 260 | | |

| THERMAL RESISTANCE RATINGS | | | | | | |
|---|--------------|-------------------|---------|---------|------|--|
| PARAMETER | | SYMBOL | TYPICAL | MAXIMUM | UNIT | |
| Maximum junction-to-ambient ^{b, f} | t ≤ 5 s | R _{thJA} | 28 | 36 | °C/W | |
| Maximum junction-to-case (drain) | Steady state | R _{thJC} | 5.3 | 6.5 | C/W | |

Notes

a. Package limited

b. Surface mounted on 1" x 1" FR4 board

c. t = 5 s

d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

f. Maximum under steady state conditions is 80 °C/W

S12-2394-Rev. A, 15-Oct-12

1

Document Number: 62779

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SiA483DJ

| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNIT | |
|---|--------------------------|---|------|-------|-------|----------|--|
| Static | | | | • | • | • | |
| Drain-source breakdown voltage | V _{DS} | $V_{GS} = 0, I_D = -250 \ \mu A$ | -30 | - | - | V | |
| V _{DS} temperature coefficient | $\Delta V_{DS}/T_J$ | L 050 A | - | -21 | - | | |
| V _{GS(th)} temperature coefficient | $\Delta V_{GS(th)}/T_J$ | I _D = -250 μΑ | - | 4.6 | - | mV/°C | |
| Gate-source threshold voltage | V _{GS(th)} | $V_{DS} = V_{GS}$, $I_D = -250 \ \mu A$ | -1 | - | -2.2 | V | |
| Gate-source leakage | I _{GSS} | $V_{DS} = 0 V, V_{GS} = \pm 20 V$ | - | - | ± 100 | nA | |
| Zere gete veltage drain ourrent | 1 | $V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$ | - | - | -1 | | |
| Zero gate voltage drain current | IDSS | V_{DS} = -30 V, V_{GS} = 0 V, T_{J} = 55 °C | - | - | -10 | μA 10 | |
| On-state drain current ^a | I _{D(on)} | $V_{DS} \leq$ -5 V, V_{GS} = -10 V | -10 | - | - | Α | |
| Drain-source on-state resistance ^a | Р | $V_{GS} = -10 \text{ V}, \text{ I}_{D} = -5 \text{ A}$ | - | 0.016 | 0.021 | Ω | |
| Drain-source on-state resistance ~ | R _{DS(on)} | $V_{GS} = -4.5 \text{ V}, \text{ I}_{D} = -3 \text{ A}$ | - | 0.024 | 0.030 | | |
| Forward transconductance a | 9 _{fs} | $V_{DS} = -10 \text{ V}, \text{ I}_{D} = -5 \text{ A}$ | - | 23 | - | S | |
| Dynamic ^b | | | | | | | |
| Input capacitance | C _{iss} | | - | 1550 | - | | |
| Output capacitance | C _{oss} | V_{DS} = -15 V, V_{GS} = 0 V, f = 1 MHz | - | 175 | - | pF | |
| Reverse transfer capacitance | C _{rss} | | - | 150 | - | | |
| Tatal asta shawar | 0 | V_{DS} = -15 V, V_{GS} = -10 V, I_{D} = -10 A | - | 29 | 45 | | |
| Total gate charge | Qg | | - | 14 | 21 | | |
| Gate-source charge | Q _{gs} | V_{DS} = -15 V, V_{GS} = -4.5 V, I_D = -10 A | - | 4.4 | - | nC | |
| Gate-drain charge | Q _{gd} | | - | 4.8 | - | | |
| Gate resistance | R _g f = 1 MHz | | 0.7 | 3.7 | 7.4 | Ω | |
| Turn-on delay time | t _{d(on)} | | - | 37 | 80 | | |
| Rise time | tr | $V_{DD} = -15 \text{ V}, \text{ R}_{\text{L}} = 1.9 \Omega$ | - | 30 | 60 | - | |
| Turn-off delay time | t _{d(off)} | $I_D \cong$ -8 A, V_{GEN} = -4.5 V, R_g = 1 Ω | - | 25 | 50 | | |
| Fall time | t _f | | - | 8 | 20 | | |
| Turn-on delay time | t _{d(on)} | | - | 10 | 10 | ns | |
| Rise time | t _r | V_{DD} = -15 V, R _L = 1.9 Ω | - | 10 | 20 | | |
| Turn-off delay time | t _{d(off)} | $I_D\cong$ -8 A, V_{GEN} = -10 V, R_g = 1 Ω | - | 27 | 55 | | |
| Fall time | t _f | | - | 9 | 20 | | |
| Drain-Source Body Diode Characterist | ics | | | | • | | |
| Continuous source-drain diode current | IS | $T_{C} = 25 \ ^{\circ}C$ | - | - | -12 | ٨ | |
| Pulse diode forward current | I _{SM} | | - | - | -40 | A | |
| Body diode voltage | V _{SD} | $I_{\rm S} = -8$ A, $V_{\rm GS} = 0$ V | - | -0.8 | -1.2 | V | |
| Body diode reverse recovery time | t _{rr} | | - | 17 | 40 | ns | |
| Body diode reverse recovery charge | Q _{rr} | I _F = -8 A, di/dt = 100 A/µs, | - | 10 | 20 | nC | |
| Reverse recovery fall time | t _a | $T_J = 25 \ ^{\circ}C$ | - | 10 | - | | |
| Reverse recovery rise time | t _b | | - | 7 | - | ns | |

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

b. Guaranteed by design, not subject to production testing

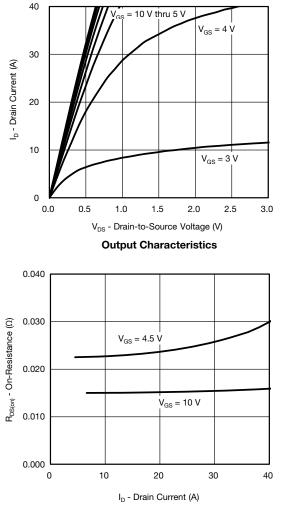
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2

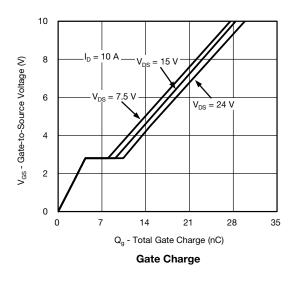
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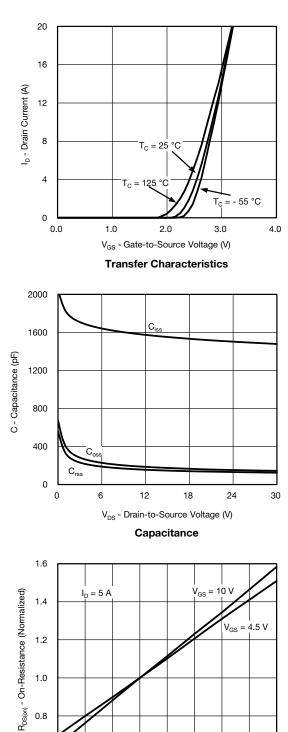


TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



On-Resistance vs. Drain Current and Gate Voltage





- 50 - 25 0 25 50 75 100 125 150 $T_{\rm J} \mbox{ - Junction Temperature (°C)}$

On-Resistance vs. Junction Temperature

S12-2394-Rev. A, 15-Oct-12

3

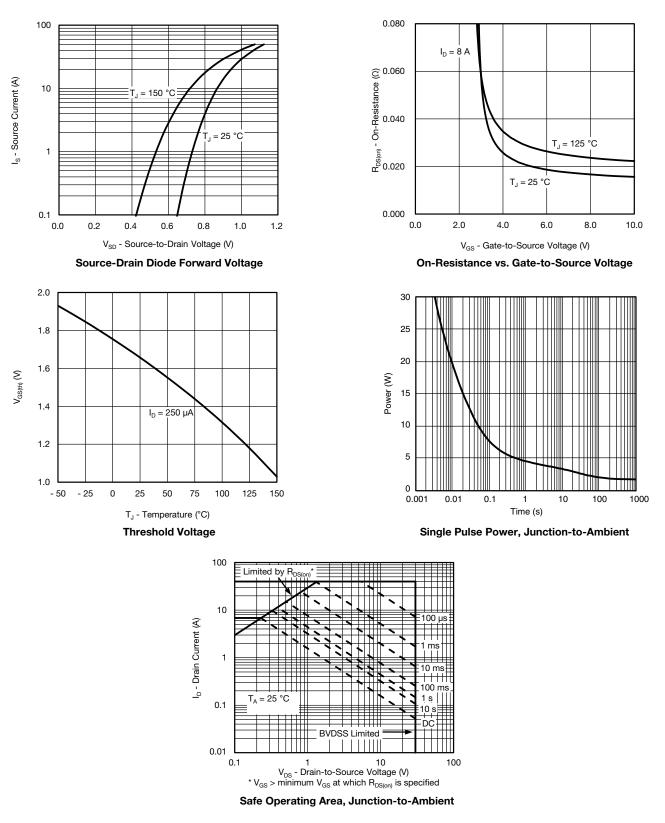
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



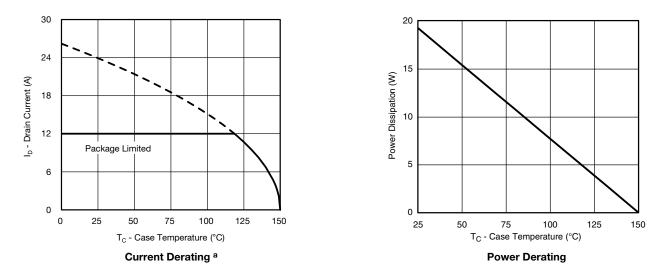
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

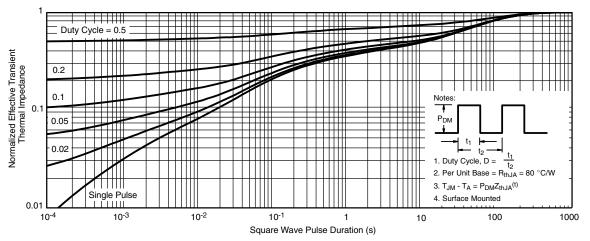


Note

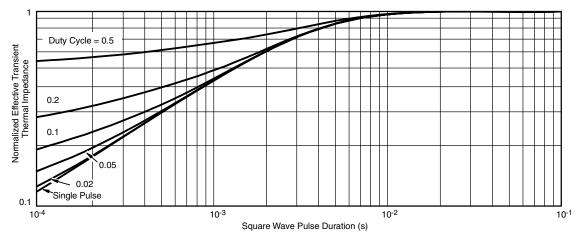
a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

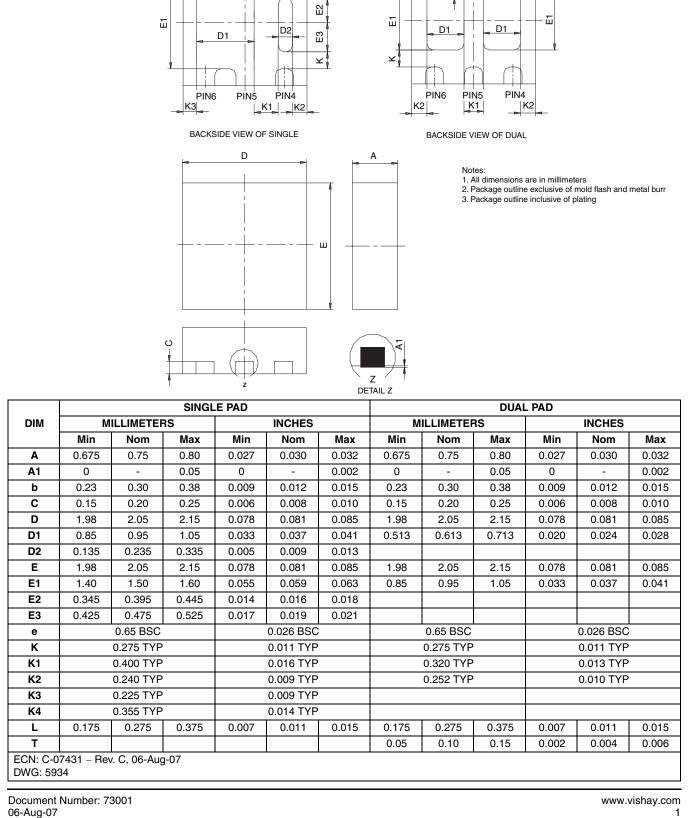


Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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PowerPAK[®] SC70-6L

b PIN2 PIN1 PIN3 _ ₹

Package Information

b

PIN3

__ ₿

PIN2

PIN1

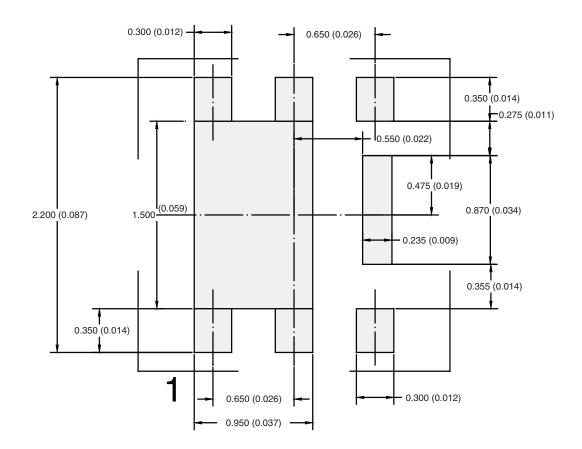
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RECOMMENDED PAD LAYOUT FOR PowerPAK[®] SC70-6L Single



Dimensions in mm/(Inches)

Return to Index

APPLICATION NOTE



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